Primer on Semiconductors

Unit 3: Equilibrium Carrier Concentrations

Lecture 3.4: Carrier concentration vs. doping density

Mark Lundstrom

Iundstro@purdue.edu
Electrical and Computer Engineering
Purdue University
West Lafayette, Indiana USA



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Carrier concentrations vs. Fermi level

Electrons

$$n_0 = N_C \mathcal{F}_{1/2} \left[\left(E_F - E_C \right) / k_B T \right] \text{ m}^{-3}$$

$$N_{C} = \frac{1}{4} \left(\frac{2m_{n}^{*} k_{B} T}{\pi \hbar^{2}} \right)^{3/2}$$

nondegenerate:

$$n_0 = N_C e^{(E_F - E_C)/k_B T}$$

$$n_0 = n_i e^{(E_F - E_i)/k_B T}$$

Holes

$$p_0 = N_V \mathcal{F}_{1/2} [(E_V - E_F)/k_B T] \text{ m}^{-3}$$

$$N_{V} = \frac{1}{4} \left(\frac{2m_{p}^{*} k_{B} T}{\pi \hbar^{2}} \right)^{3/2}$$

nondegenerate:

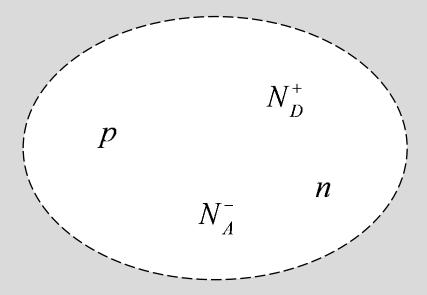
$$p_0 = N_V e^{(E_V - E_F)/k_B T}$$

$$p_0 = n_i e^{(E_i - E_F)/k_B T}$$

Space charge density

What is the net charge in this region?

$$\rho = q \left[p - n + N_D^+ - N_A^- \right] \quad C/m^3$$



bulk, uniform semiconductor

Space charge neutrality

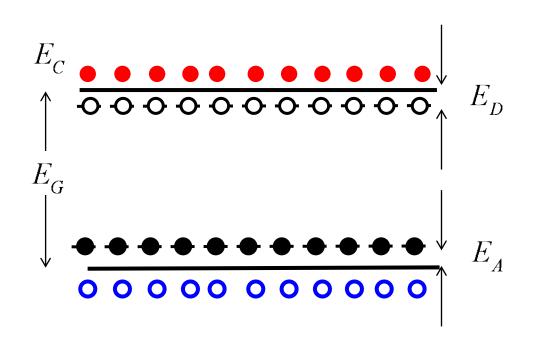
Nature abhors a vacuum. Nature also abhors a charge.

Mobile charges (electrons and holes) will be attracted to the immobile ionized dopants), so that the net charge is zero.

$$\rho = q [p - n + N_D^+ - N_A^-] = 0$$

Almost uniform semiconductors will be nearly neutral, but with strong non-uniformities (e.g. PN junctions), there will be a space charge.

Fully ionized dopants



All donors have donated their electrons to the conduction band and are now positively charged.

$$N_D^+ = N_D$$
 $N_A^- = N_A$

All acceptors have accepted an electron from the valence band and are now negatively charged.

Space charge neutrality again

$$\rho = q \left[p - n + N_D^+ - N_A^- \right] = 0$$

Assume **fully ionized dopants** (this will typically be the case for good dopants near and above room temperature).

$$\rho = q \left[p_0 - n_0 + N_D - N_A \right] = 0 \qquad n_0 p_0 = n_i^2$$

Assuming that we know how many dopants we introduced into the semiconductor, these are two equations in two unknowns -p and n.

Solving for the carrier density

$$p_0 - n_0 + N_D^+ - N_A^- = 0$$

2) Fully ionized dopants:
$$p_0 - n_0 + N_D - N_A = 0$$

$$p_0 - n_0 + N_D - N_A = 0$$

$$n_0 p_0 = n_i^2$$

$$\frac{n_i^2}{n_0} - n_0 + N_D - N_A = 0$$

$$p_0 - \frac{n_i^2}{p_0} + N_D - N_A = 0$$

Result: N-type

$$\frac{n_i^2}{n_0} - n_0 + N_D - N_A = 0$$

$$n_{0} = \frac{N_{D} - N_{A}}{2} + \left[\left(\frac{N_{D} - N_{A}}{2} \right)^{2} + n_{i}^{2} \right]^{1/2}$$

$$p_{0} = \frac{n_{i}^{2}}{n_{0}}$$

$$p_0 = \frac{n_i^2}{n_0}$$

Result: P-type

$$p_0 - \frac{n_i^2}{p_0} + N_D - N_A = 0$$

$$p_{0} = \frac{N_{A} - N_{D}}{2} + \left[\left(\frac{N_{A} - N_{D}}{2} \right)^{2} + n_{i}^{2} \right]^{1/2}$$

$$n_{0} = \frac{n_{i}^{2}}{p_{0}}$$

$$n_0 = \frac{n_i^2}{p_0}$$

Example 1

Consider Si doped with phosphorus at $N_D = 2.00 \times 10^{15} \text{ cm}^{-3}$ The temperature is 300 K. What are *n* and *p*?

Recall that at 300 K in Si, $n_i = 1.00 \times 10^{10} \text{ cm}^{-3}$

Assume that the donors are fully ionized.

$$n_{0} = \frac{N_{D} - N_{A}}{2} + \left[\left(\frac{N_{D} - N_{A}}{2} \right)^{2} + n_{i}^{2} \right]^{1/2} = \frac{N_{D}}{2} + \left[\left(\frac{N_{D}}{2} \right)^{2} + n_{i}^{2} \right]^{1/2}$$

$$N_{D} >> n_{i} \qquad n_{0} = N_{D} = 2.00 \times 10^{15} \text{ cm}^{-3}$$

$$p_{0} = n_{i}^{2} / n_{0} \qquad p_{0} = \left(10^{10} \right)^{2} / 2 \times 10^{15} = 5 \times 10^{4} \text{ cm}^{-3}$$

Example 2

Consider Si doped with phosphorus at $N_D = 2.00 \times 10^{15} \text{ cm}^{-3}$ and Boron at $N_A = 1.00 \times 10^{15} \text{ cm}^{-15}$.

The temperature is 300 K. What are n and p?

$$n_{0} = \frac{N_{D} - N_{A}}{2} + \left[\left(\frac{N_{D} - N_{A}}{2} \right)^{2} + n_{i}^{2} \right]^{1/2}$$

$$N_{D} - N_{A} >> n_{i} \qquad n_{0} = N_{D} - N_{A}$$

$$p_0 = n_i^2 / n_0$$
 $n_0 = 1.00 \times 10^{15} \text{ cm}^{-3}$
$$p_0 = n_i^2 / n_0$$
 $p_0 = (10^{10})^2 / 1 \times 10^{15} = 1 \times 10^5 \text{ cm}^{-3}$

Conclusion

When the net doping density is much greater than the intrinsic carrier concentration and the dopants are fully ionized, then

$$n_0 = N_D - N_A$$
 $p_0 = n_i^2 / (N_D - N_A)$ N-type $N_D > N_A$

$$p_0 = N_A - N_D$$
 $n_0 = n_i^2 / (N_A - N_D)$ P-type $N_A > N_D$

Summary

